

CS/B.Tech/IT/Odd/Sem-7th/IT-705D/2014-15

IT-705D

MICROELECTRONICS AND VLSI DESIGN

Time Allotted: 3 Hours

Full Marks: 70

The questions are of equal value.

The figures in the margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

GROUP A (Multiple Choice Type Questions)

1. Answer any *ten* questions. 10×1 = 10

(i) VHDL is acronym of

- (A) verilog hardware description language
- (B) very high speed insulated chip hardware description language
- (C) very high speed integrated circuit hardware description language
- (D) none of these.

(ii) For depletion type n-MOS

- (A) the threshold voltage is + ve
- (B) the threshold voltage is – ve
- (C) the threshold voltage is + ve and – ve
- (D) all of these

(iii) BiCMOS means

- (A) two BJT circuits
- (B) two CMOS circuits
- (C) both BJT and CMOS circuits
- (D) none of these

(iv) NAND flash memory is constructed with.

- (A) 2 parallel cells
- (B) 16 cells in series
- (C) 8 cells in parallel
- (D) none

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(v) Latch up is defined as the.

- (A) low impedance
- (B) high impedance
- (C) medium impedance
- (D) none

(vi) Designable parameters are.

- (A) commonly grouped
- (B) loosely coupled
- (C) tightly coupled
- (D) none

(vii) Noise parameters are treated as.

- (A) static variables.
- (B) random variables.
- (C) constants.
- (D) none

(viii) A circuit performance major is used to monitor

- (A) functionality of circuit
- (B) durability of circuit
- (C) accountability of circuit
- (D) none

(ix) Designable parameters are

- (A) deterministic
- (B) probabilistic
- (C) indeterministic
- (D) none

(x) Which among the following requires lowest design cycle time?

- (A) semi-custom ASIC
- (B) full-custom ASIC
- (C) standard cell-based design
- (D) FPGA

(xi) Different FPGA programming technologies are based on

- (A) SRAM
- (B) EPROM
- (C) Anti-fuse
- (D) all of these

(xii) The model parameter LAMDA (λ) in a MOS structure stands for

- (A) flicker noise coefficient
- (B) transit time
- (C) channel length modulation
- (D) transconductance

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GROUP B
(Short Answer Type Questions)

Answer any *three* questions.

3×5 = 15

2. (a) What is Layout? 1
- (b) Draw the Circuit diagram and Layout of CMOS inverter and explain. 2+2
3. (a) What is Stick Diagram? 1
- (b) Draw the Stick diagram of $F = (A + B + C) \cdot D$ and calculate the area using the λ -rule. 4
4. Explain the Y-chart of VLSI design flow. 5
5. What is an FPGA? How is it different from CPLD? What are its advantages? 2+2+1
6. (a) What is ASIC? Give its classification. 2
- (b) Why VLSI design flow is often called as cycle? Explain. 3
7. Write VHDL code in behavioral mode for a full Adder. 5

GROUP C
(Long Answer Type Questions)

Answer any *three* questions.

3×15 = 45

8. (a) Explain the n -well CMOS fabrication process with necessary diagram. 10
- (b) Draw the CMOS NAND gate and CMOS NOR gate using Layout technique. 5
9. (a) Explain with example and proper block diagram the Standard Cell based design. 8
- (b) Explain the Moore's Law for both processor and Memory design. 3
- (c) Explain λ -rule. 4

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- 10.(a) Draw the CMOS full Adder circuit. Hence draw the corresponding mask layout diagram. 3+5

(b) Explain the static and dynamic power losses in VLSI design. 4

(c) Why pull up networks are made of p -MOS transistor and Pull down networks are made of n -MOS transistor. 4

- 11.(a) Draw the circuit diagram of CMOS inverter and calculate the followings (Symbols are of usual meaning) 3+3+3

(i) V_{IL}

(ii) V_{OH}

(iii) V_{th}

(b) Explain the voltage transfer characteristic VTC of the Inverter. 4

(c) What is uncertain or transition region of the VTC curve, explain. 2

- 12.(a) Draw the circuit diagram of CMOS NOR based SR Latch and NAND based SR latch. 2.5+2.5

(b) Draw the circuit diagram of CMOS master slave JK flip flop and explain its timing diagram. 4+3

(c) Draw the circuit diagram of CMOS clocked D-flip flop 3

13. Write short notes on any *three* of the following: 3×5

(a) Dynamic logic

(b) Photo-lithography

(c) Ion-implantation

(d) PLA

(e) Latch up problem in CMOS

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